No.2124A

DS462

Silicon Epitaxial Planar Type

High-Voltage Switching Diode

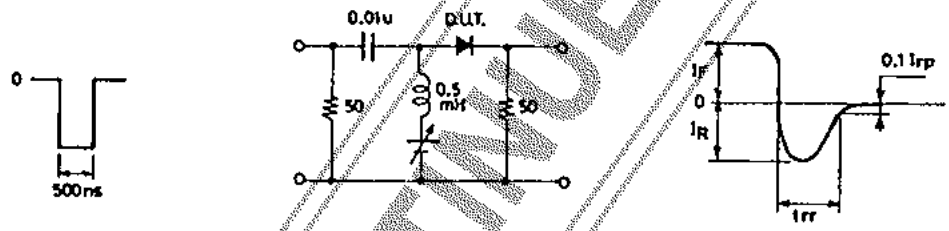
Absolute Maximum Ratings at Ta = 25°C

				unit
Peak Reverse Voltage	V_{RM}		−250	V
Reverse Voltage	V_R		−200	V
Peak Forward Current	I_{FM}		600	mA
Average Rectified Current	I_O		200	mA
Surge Forward Current	I_{FSM}	10msec pulse	2000	mA
Allowable Power Dissipation	P		400	mW
Junction Temperature	Tj		175	°C
Storage Temperature	Tstg		−65 to +175	°C

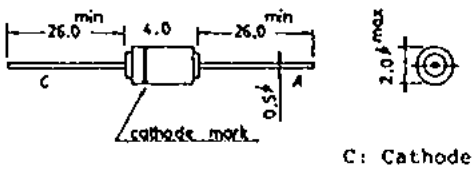
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Forward Voltage	V_F1	$I_F = 1mA$			0.8	V
	V_F2	$I_F = 100mA$		0.95	1.2	V
Reverse Current	I_R	$V_R = -200V$			−0.5	μA
Interterminal Capacitance	c	$V_R = 0V, f = 1MHz$		1.0		pF
Reverse Recovery Time	t_{rr}	$I_F = I_R = 10mA, R_L = 50\Omega$			60	ns

Reverse Recovery Time Test Circuit



Case Outline 1080
(unit : mm)



C : Cathode
A : Anode

Specifications and information herein are subject to change without notice.

SANYO Electric Co.,Ltd. Semiconductor Overseas Marketing Div.
Natsume Bldg., 18-6, 2-chome, Yushima, Bunkyo-ku, TOKYO 113 JAPAN